**Vishay Semiconductors** 

Hyperfast Rectifier, 30 A FRED Pt<sup>®</sup> G5



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## LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS						
I <sub>F(AV)</sub> 30 A						
V <sub>R</sub>	1200 V					
V <sub>F</sub> at I <sub>F</sub> at 125 °C	2.1 V					
t <sub>rr</sub>	26 ns					
T <sub>J</sub> max.	175 °C					
Package	2L TO-220AC					
Circuit configuration	Single					

### **FEATURES**

- Hyperfast and optimized Q<sub>rr</sub>
- Best in class forward voltage drop and switching RoHS
   losses trade off
   HALOGEN
- Optimized for high speed operation
- 175 °C maximum operating junction temperature
- Polyimide passivation
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

### **DESCRIPTION / APPLICATIONS**

Featuring a unique combination of low conduction and switching losses, this rectifier is the right choice for high frequency converters, both soft switched / resonant.

Specifically designed to improve efficiency of PFC and output rectification stages of EV / HEV battery charging stations, booster stage of solar inverters and UPS applications, these devices are perfectly matched to operate with MOSFETs or high speed IGBTs.

### **MECHANICAL DATA**

Case: 2L TO-220AC

Molding compound meets UL 94 V-0 flammability rating

**Terminals:** matte tin plated leads, solderable per J-STD-002 and JESD 22-B102

Polarity: as per marking device details

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Repetitive peak reverse voltage	V <sub>RRM</sub>		1200	V			
Average rectified forward current	I <sub>F(AV)</sub>	T <sub>C</sub> = 83 °C, D = 0.50	30				
Non-repetitive peak surge current	I <sub>FSM</sub>	$T_{C}$ = 83 °C, $t_{p}$ = 10 ms, sine wave	190	A			
Repetitive peak forward current	I <sub>FRM</sub>	T <sub>C</sub> = 45 °C, D = 0.50, f = 20 kHz	60				
Operating junction and storage temperature	T <sub>J</sub> , T <sub>Stg</sub>		-55 to +175	°C			

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 $^{\circ}$ C unless otherwise specified)								
PARAMETER	SYMBOL	BOL TEST CONDITIONS MIN.		TYP.	MAX.	UNITS		
Breakdown voltage, blocking voltage	V <sub>BR</sub> , V <sub>R</sub>	I <sub>R</sub> = 100 μA	1200	-	-			
Forward voltage	V <sub>F</sub>	I <sub>F</sub> = 30 A	-	2.6	3.3	V		
		I <sub>F</sub> = 30 A, T <sub>J</sub> = 125 °C	-	2.1	-			
	I <sub>R</sub>	$V_{R} = V_{R}$ rated	-	-	50			
Reverse leakage current		$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	-	500	μA		
Junction capacitance	CT	V <sub>R</sub> = 200 V	-	17	-	pF		
Series inductance	L <sub>S</sub>	Measured to lead 5 mm from package body	-	8	-	nH		

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 1
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<b>DYNAMIC RECOVERY CHARACTERISTICS</b> ( $T_J = 25$ °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS	
		I <sub>F</sub> = 1.0 A, dI <sub>F</sub> /dt =	$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 100 \text{ A}/\mu\text{s}, V_R = 30 \text{ V}$		26	47		
Reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	100	-	ns	
		T <sub>J</sub> = 125 °C		-	150	-		
Peak recovery current		T <sub>J</sub> = 25 °C	I <sub>F</sub> = 20 A dI <sub>F</sub> /dt = 600 A/μs V <sub>R</sub> = 400 V	-	12	-	A	
	I <sub>RRM</sub>	T <sub>J</sub> = 125 °C		-	22	-		
Powerse receivery charge	0	T <sub>J</sub> = 25 °C		-	530	-	nC	
Reverse recovery charge	Q <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	1650	-		
Reverse recovery time	+	T <sub>J</sub> = 25 °C		-	80	-	ns	
neverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	120	-	115	
Poole recovery ourrent		T <sub>J</sub> = 25 °C	I <sub>F</sub> = 30 A dI <sub>F</sub> /dt = 1000 A/μs V <sub>R</sub> = 800 V	-	22	-	A	
Peak recovery current	I <sub>RRM</sub>	T <sub>J</sub> = 125 °C		-	37	-		
Reverse recovery charge	0	T <sub>J</sub> = 25 °C		-	900	-		
	Q <sub>rr</sub>	T <sub>J</sub> = 125 °C	]	-	2400	-	nC	

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Thermal resistance, junction-to-case	R <sub>thJC</sub>		-	-	1.1	°C/W	
147.1.1.1			-	2.0	-	g	
Weight			-	0.07	-	oz.	
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)	
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-55	-	175	°C	
Marking device		Case style: 2L TO-220AC	E5TX3012				

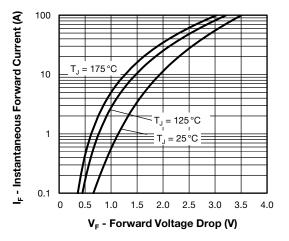


Fig. 1 - Typical Forward Voltage Drop Characteristics

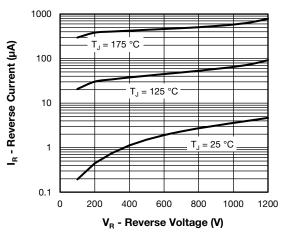


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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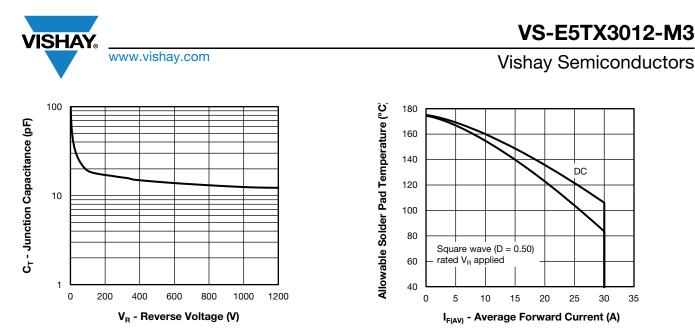


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

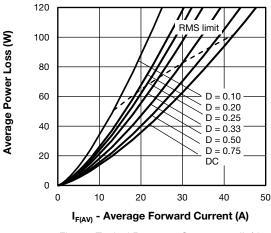


Fig. 5 - Typical Recovery Current vs. dl<sub>F</sub>/dt

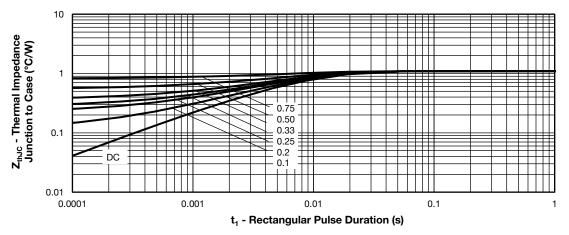


Fig. 6 - Thermal Impedance  $Z_{thJC}$  Characteristics

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# VS-E5TX3012-M3

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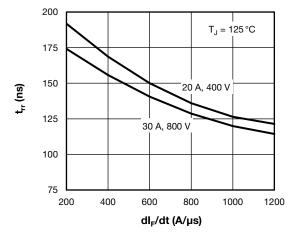


Fig. 7 - Typical Reverse Recovery Time vs. dI<sub>F</sub>/dt

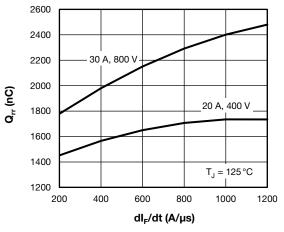


Fig. 8 - Typical Stored Charge vs. dl<sub>F</sub>/dt

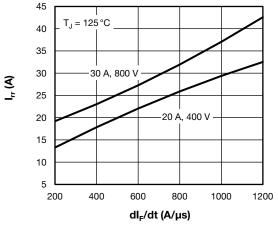


Fig. 9 - Typical Recovery Current vs. dl<sub>F</sub>/dt



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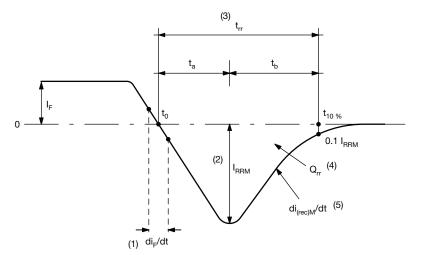


Fig. 10 - Reverse Recovery Waveform and Definitions

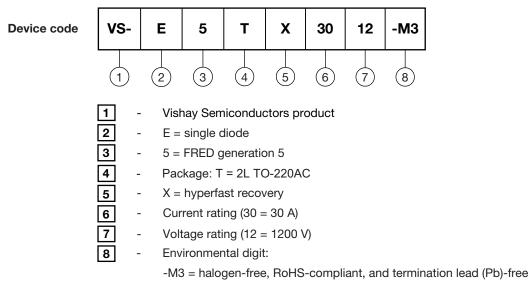
### Notes

- (1) di<sub>F</sub>/dt rate of change of current through zero crossing
- <sup>(2)</sup> I<sub>RRM</sub> peak reverse recovery current
- $^{(3)}$  t<sub>rr</sub> reverse recovery time measured from t<sub>0</sub>, crossing point of negative going I<sub>F</sub>, to point t<sub>10%</sub>, 0.1 I<sub>RRM</sub>
- $^{(4)}~~\text{Q}_{rr}$  area under curve defined by  $t_0$  and  $t_{10~\%}$

$$Q_{rr} = \int\limits_{t_0}^{t_{10}\,\%} I(t)dt$$

 $^{(5)}$  di<sub>(rec)</sub>M/dt - peak rate of change of current during t<sub>b</sub> portion of t<sub>rr</sub>

### **ORDERING INFORMATION TABLE**



ORDERING INFORMATION (Example)							
PREFERRED P/N	RED P/N QUANTITY PER TUBE MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION						
VS-E5TX3012-M3	50	1000	Antistatic plastic tube				

LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?96154
Part marking information	www.vishay.com/doc?95391

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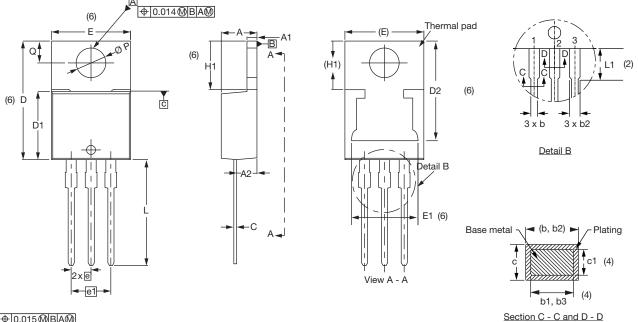
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## **3L TO-220AB**

### **DIMENSIONS** in millimeters and inches



⊕0.015@BA@





SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STINDUL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.50	2.92	0.098	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.35	0.585	0.604	3
D1	8.38	9.02	0.330	0.355	

_		
Conforms to JEDEC <sup>®</sup>	outline	<b>TO-220AB</b>

SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STINDOL	MIN.	MAX.	MIN.	MAX.	NOTES
D2	11.68	13.30	0.460	0.524	6, 7
Ш	10.11	10.51	0.398	0.414	3, 6
E1	6.86	8.89	0.270	0.350	6
е	2.41	2.67	0.095	0.105	
e1	4.88	5.28	0.192	0.208	
H1	6.09	6.48	0.240	0.255	6
L	13.52	14.02	0.532	0.552	
L1	3.32	3.82	0.131	0.150	2
ØР	3.54	3.91	0.139	0.154	
Q	2.60	3.00	0.102	0.118	

#### Notes

<sup>(2)</sup> Lead dimension and finish uncontrolled in L1

- <sup>(4)</sup> Dimension b1, b3, and c1 apply to base metal only
- (5) Controlling dimensions: inches
- <sup>(6)</sup> Thermal pad contour optional within dimensions E, H1, D2, and E1
- <sup>(7)</sup> Outline conforms to JEDEC<sup>®</sup> TO-220, except D2

Revision: 13-Jun-2019

 $<sup>^{(1)}\,</sup>$  Dimensioning and tolerancing as per ASME Y14.5M-1994

<sup>(3)</sup> Dimension D, D1, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body



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